	<u>Unean</u>
Name:	(A)
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Inviailator's Signature:	

CS/M.Tech (ECE-VLSI)/SEM-2/MVLSI-205 A/2013 2013

RF CIRCUITS & SYSTEMS

Time Allotted: 3 Hours Full Marks: 70

The figures in the margin indicate full marks.

Candidates are required to give their answers in their own words as far as practicable.

Question No. 1 is compulsory and attempts any 4 from the rest.

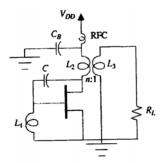
1. Answer the following question:

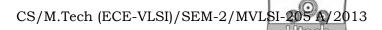
- $7 \times 2 = 14$
- a) What is Heterostructure ? Is this structure superior to homostructure ? Explain.
- b) Write down the characteristics of high frequency BJT used in RF range.
- c) Explain resonant tunneling phenomenon?
- d) Differentiate active and passive RF components
- e) Why T parameters are necessary for the analysis of RF networks.
- f) What are the basic use of Smith chart in the RF application field.
- g) What is the use of PLL circuit.

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- 2. Explain the principle of operation of a microwave tunnel diode. Show the V-I characteristic of a tunnel diode. A microwave tunnel diode has a negative resistance R_l and the resonant circuit has a circuit resistance R_l . Derive equation for the gain of a microwave tunnel diode amplifier. 3 + 4 + 7
- What are the basic elements of Phase Locked Loop circuit?
 What is Phase Noise in PLL circuit & describe the effect of it? Explain the operation of VCO tuning. Describe the operation of PLL frequency synthesizer.
 3 + 4 + 3 + 4
- 4. What is Barkhausen criterion? Describe the operation of crystal oscillator. Explain the electronic tuning of oscillator. The Hartley circuit shown in Figure below is oscillating at 150 MHz. If the transconductance gm of the FET is 4.5mS, the load resistance RL is 50Ω , and there is no coupling between L1 and L2 whereas L2 and L3 are tightly coupled, find the values of the circuit components. Consider L1 = L2 = InH.





- 5. Write short note any *four*:
 - a) Frequency divider
 - b) Microwave detector
 - c) Microwave mixer
 - d) Stability of active network
 - e) T parameter
 - f) RF integrated device
- Explain the working principle of directional coupler. What are RF power combiners and splitters? Write down the characteristics of splitter/combiner circuits. Explain 90 degree splitter/combiner.
 4 + 3 + 3 + 4
- 7. What are reciprocal network and symmetrical network? Why scattering parameters are used for the analysis of a network? Show the scattering matrix. Obtain expressions for scattering parameters.

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